

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A self light-emitting device comprising:

- an opaque electrode over a substrate;
- an EL layer over the opaque electrode;
- a transparent electrode over the EL layer; and
- an inert gas filled in a space between the transparent electrode and a cover material,

wherein each of said EL layer and said transparent electrode has a film thickness (d) in which there is no occurrence of a guided light[[.]], and

wherein a light generated in said EL layer is emitted to said cover material side.

2. (Original) A device according to claim 1, wherein said film thickness (d) satisfies a formula $d \leq \lambda / (4n)$, when a light with a wavelength generated by the EL layer passes through a medium with a refractive index n.

3. (Currently amended) A self light-emitting device comprising:

- an opaque electrode over a substrate;
- an EL layer over the opaque electrode, said EL layer having a light-emitting layer;
- a transparent electrode over the EL layer;
- an inert gas is filled in a space between the transparent electrode and a cover material; and
- a buffer layer provided between said light-emitting layer and said transparent electrode or between said light-emitting layer and said opaque electrode,

wherein each of said EL layer and said transparent electrode has a film thickness (d) in which there is no occurrence of a guided light[[.]], and

wherein a light generated in said EL layer is emitted to said cover material side.

4. (Original) A device according to claim 3, wherein said film thickness (d) satisfies a formula $d \leq \lambda / (4n)$, when a light with a wavelength generated by the EL layer passes through a medium with a refractive index n.

5. (Currently amended) A self light-emitting device having a pixel portion comprising a semiconductor device and an EL element electrically connected to the semiconductor device formed on a substrate, said EL element comprising:

an opaque electrode;

an EL layer over the an opaque electrode;

a transparent electrode over the EL layer; and

an inert gas filled in a space between the transparent electrode and a cover material,

wherein each of said EL layer and said transparent electrode has a film thickness (d) in which there is no occurrence of a guided light[[.]] , and

wherein a light generated in said EL layer is emitted to said cover material side.

6. (Original) A device according to claim 5, wherein said film thickness (d) satisfies a formula $d \leq \lambda / (4n)$, when a light with a wavelength generated by the EL layer passes through a medium with a refractive index n.

7. (Currently amended) A self light-emitting device having a pixel portion comprising a semiconductor device and an EL element electrically connected to the semiconductor device formed on a substrate, said EL element comprising:

an opaque electrode;
an EL layer over the opaque electrode, said EL layer having a light-emitting layer;
a transparent electrode over the EL layer;
an inert gas filled in a space between the transparent electrode and a cover material; and
a buffer layer provided between said light-emitting layer and said transparent electrode or between said light-emitting layer and said opaque electrode,

wherein each of said EL layer and said transparent electrode has a film thickness (d) in which there is no occurrence of a guided light[[.]], and

wherein a light generated in said EL layer is emitted to said cover material side.

8. (Original) A device according to claim 7, wherein said film thickness (d) satisfies a formula $d \leq \lambda / (4n)$, when a light with a wavelength generated by the EL layer passes through a medium with a refractive index n.

9. (Currently amended) A self light-emitting device having a pixel portion comprising:

a plurality of opaque electrodes arranged in stripe shapes over a substrate;
an EL layer over the plurality of opaque electrodes;
a plurality of transparent electrodes over the EL layer, the plurality of transparent electrodes

provided in stripe shapes so as to be orthogonal to the plurality of opaque electrodes; and
an inert gas filled in a space between the transparent electrode and a cover material,
wherein each of said EL layer and said transparent electrode are film thickness (d) in which
there is no occurrence of a guided light[.]], and
wherein a light generated in said EL layer is emitted to said cover material side.

10. (Original) A device according to claim 9, wherein said film thickness (d) satisfies a formula $d \leq \lambda / (4n)$, when a light with a wavelength generated by the EL layer passes through a medium with a refractive index n.

11. (Currently amended) A self light-emitting device having a pixel portion comprising:
a plurality of opaque electrodes arranged in stripe shapes over a substrate;
an EL layer over the plurality of opaque electrodes;
a plurality of transparent electrodes over the EL layer, the plurality of the transparent electrodes provided in stripe shapes so as to be orthogonal to the plurality of opaque electrodes; and
an inert gas filled in a space between the transparent electrode and a cover material; and
a buffer layer provided between said EL layer and said transparent electrode or between said EL layer and said opaque electrode,
wherein each of said EL layer and said transparent electrode has a film thickness (d) in which
there is no occurrence of a guided light[.]], and
wherein a light generated in said EL layer is emitted to said cover material side.

12. (Original) A device according to claim 11, wherein said film thickness (d) satisfies a formula $d \leq \lambda/(4n)$, when a light with a wavelength generated by the EL layer passes through a medium with a refractive index n.